Y-J Cho

List of Publications by Citations

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42 papers	892 citations	15 h-index	29 g-index
45 ext. papers	1,046 ext. citations	4 avg, IF	3.88 L-index

#	Paper	IF	Citations
42	Valence-band anticrossing in mismatched III-V semiconductor alloys. *Physical Review B*, **2007**, 75,	3.3	310
41	Deep ultraviolet emission in hexagonal boron nitride grown by high-temperature molecular beam epitaxy. *2D Materials*, **2017**, 4, 021023	5.9	73
40	Hexagonal Boron Nitride Tunnel Barriers Grown on Graphite by High Temperature Molecular Beam Epitaxy. *Scientific Reports*, **2016**, 6, 34474	4.9	48
39	The new nitrides: layered, ferroelectric, magnetic, metallic and superconducting nitrides to boost the GaN photonics and electronics eco-system. *Japanese Journal of Applied Physics*, **2019**, 58, SC0801	1.4	43
38	Strain-Engineered Graphene Grown on Hexagonal Boron Nitride by Molecular Beam Epitaxy. *Scientific Reports*, **2016**, 6, 22440	4.9	36
37	Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV (AlGa)O on m-plane sapphire. *Science Advances*, **2021**, 7,	14.3	35
36	Integrated nano-opto-electro-mechanical sensor for spectrometry and nanometrology. *Nature Communications*, **2017**, 8, 2216	17.4	30
35	Near-bandgap wavelength dependence of long-lived traveling coherent longitudinal acoustic phonons in GaSb-GaAs heterostructures. *Physical Review B*, **2006**, 74,	3.3	28
34	Dynamically controlling the emission of single excitons in photonic crystal cavities. *Nature Communications*, **2014**, 5, 5786	17.4	26
33	Investigation of magnetic and electronic coupling between two (Ga,Mn)As layers in (Ga,Mn)AsGaAs(Ga,Mn)As magnetic tunnel junctions. *Applied Physics Letters*, **2007**, 91, 152109	3.4	20
32	Structural properties of InN films grown on O-face ZnO(0001) by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2012**, 100, 152105	3.4	19
31	Molecular beam homoepitaxy on bulk AlN enabled by aluminum-assisted surface cleaning. *Applied Physics Letters*, **2020**, 116, 172106	3.4	17
30	Surface control and MBE growth diagram for homoepitaxy on single-crystal AlN substrates. *Applied Physics Letters*, **2020**, 116, 262102	3.4	17
29	Effects of donor doping on Ga1MnxAs. *Applied Physics Letters*, **2008**, 93, 262505	3.4	16
28	Growth of wurtzite InN on bulk In2O3(111) wafers. *Applied Physics Letters*, **2012**, 101, 172102	3.4	15
27	Rotationally aligned hexagonal boron nitride on sapphire by high-temperature molecular beam epitaxy. *Physical Review Materials*, **2019**, 3,	3.2	15
26	Auger recombination as the dominant nonradiative recombination channel in InN. *Physical Review B* , **2013**, 87,	3.3	14

25	High temperature MBE of graphene on sapphire and hexagonal boron nitride flakes on sapphire. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2016**, 34, 02L101	1.3	14
24	Single-crystal N-polar GaN p-n diodes by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2017**, 110, 253506	3.4	12
23	Anisotropic dielectric functions, band-to-band transitions, and critical points in □Ga2O3. *Applied Physics Letters*, **2021**, 118, 062103	3.4	12
22	Raman scattering by wave-vector-dependent coupled plasmon/LO-phonon modes in n-type InN. *Physical Review B*, **2012**, 85,	3.3	9
21	Pump-probe studies of travelling coherent longitudinal acoustic phonon oscillations in GaAs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 2632-2636		9
20	High-frequency and below bandgap anisotropic dielectric constants in □(AlxGa1□)2O3 (0□□1). *Applied Physics Letters*, **2021**, 119, 092103	3.4	9
19	Thermal stability of epitaxial □Ga2O3 and (Al,Ga)2O3 layers on m-plane sapphire. *Applied Physics Letters*, **2021**, 119, 062102	3.4	8
18	High-mobility two-dimensional electron gases at AlGaN/GaN heterostructures grown on GaN bulk wafers and GaN template substrates. *Applied Physics Express*, **2019**, 12, 121003	2.4	6
17	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. *Applied Physics Letters*, **2021**, 119, 162104	3.4	6
16	Observation of the electron-accumulation layer at the surface of InN by cross-sectional micro-Raman spectroscopy. *Applied Physics Letters*, **2013**, 102, 072101	3.4	5
15	Infrared dielectric functions and Brillouin zone center phonons of □Ga2O3 compared to □Al2O3. *Physical Review Materials*, **2022**, 6,	3.2	5
14	N-polar GaN/AlN resonant tunneling diodes. *Applied Physics Letters*, **2020**, 117, 143501	3.4	5
13	Impact of substrate nitridation on the growth of InN on In2O3(111) by plasma-assisted molecular beam epitaxy. *Applied Surface Science*, **2016**, 369, 159-162	6.7	4
12	Characteristics of three-beam photoreflectance in ZnTe/GaAs with deep traps. *Solid State Communications*, **1999**, 110, 605-609	1.6	4
11	Blue (In,Ga)N light-emitting diodes with buried n +□p + tunnel junctions by plasma-assisted molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2019**, 58, 060914	1.4	3
10	Magnetic properties of MBE grown Mn4N on MgO, SiC, GaN and Al2O3 substrates. *AIP Advances*, **2020**, 10, 015238	1.5	3
9	Collapse of ferromagnetism in (Ga, Mn)As at high hole concentrations. *Semiconductor Science and Technology*, **2008**, 23, 125010	1.8	3
8	Magnetic anisotropy of ferromagnetic Ga1□MnxAs formed by Mn ion implantation and pulsed-laser melting. *Journal of Applied Physics*, **2008**, 104, 043902	2.5	3

7	In-assisted deoxidation of GaAs substrates for the growth of single InAs/GaAs quantum dot emitters. *Semiconductor Science and Technology*, **2015**, 30, 055009	1.8	2
6	Effects of Ga on the growth of InN on O-face ZnO(0001▯) by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2012**, 101, 052103	3.4	2
5	Valence band anticrossing in mismatched III-V semiconductor alloys. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 1711-1714		2
4	Vanishing of ferromagnetic order in (Ga,Mn)As films at high hole concentrations: beyond the mean field Zener model. *Journal of Applied Physics*, **2008**, 103, 07D132	2.5	1
3	GaN/AlGaN 2DEGs in the quantum regime: Magneto-transport and photoluminescence to 60 tesla. *Applied Physics Letters*, **2020**, 117, 262105	3.4	1
2	Infrared-active phonon modes and static dielectric constants in ▯(AlxGa1▯)2O3 (0.18 ▯x ▯0.54) alloys. *Applied Physics Letters*, **2022**, 120, 112202	3.4	1
1	Epitaxial Ferrimagnetic Mn4N Thin Films on GaN by Molecular Beam Epitaxy. *IEEE Transactions on Magnetics*, **2021**, 1-1	2	0